

CS 240 - The University of Illinois
Wade Fagen-Ulmschneider
August 31, 2021



Binary Addition



0b 010011+0b 001001



0b 0011+0b 0111



Negative Numbers



0b 010011-0b 001001



0b 0011-0b 0111



0b 0011 \Rightarrow 0011 -0b <u>0111</u> \Rightarrow + <u>1111</u> \Rightarrow 10010

Two's Complement



Two's Complement

Big Idea: Represent numbers signed numbers in binary in a way that:



Two's Complement

Method:



-17 =



-4 =



-1 =



-<u>18</u>



18

-<u>42</u>



-42

- <u>32</u>



Overflow Detection



-31

- <u>42</u>



Towards Multiplication



 $10 \times 2 =$



 $10 \times 4 =$



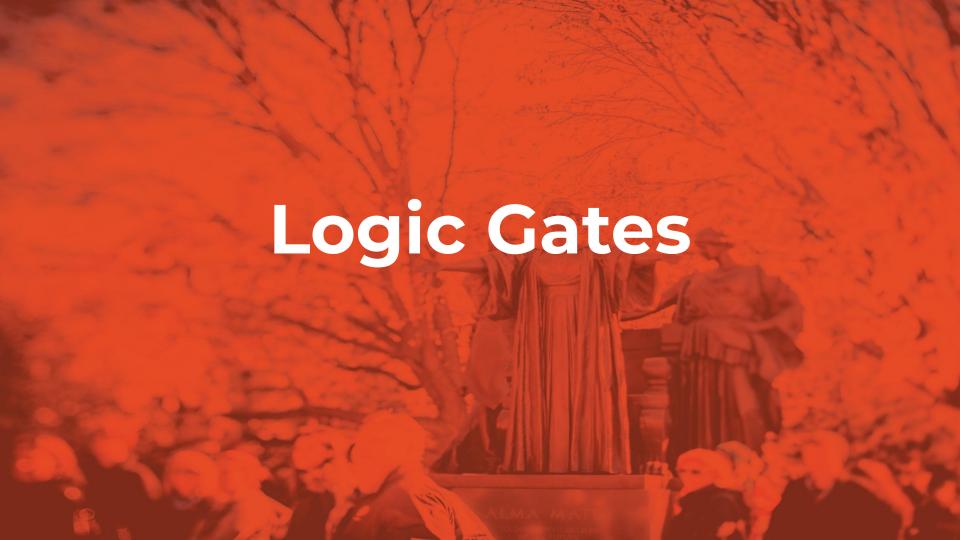
 $10 \times 9 =$



Left Shift:

Right Shift:













Functionally Complete Gate?

A	В	A&B	A B	A^B	
0	0	0	0	0	
0	1	0	1	1	
1	0	0	1	1	
1	1	1	1	0	



CMOS NOR Gates

High-Voltage Types (20-Volt Rating)

Quad 2 Input - CD4001B Dual 4 Input - CD4002B Triple 3 Input - CD4025B

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STATIC ELECTRICAL CHARACTERISTICS

CHARACTER- ISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							
	Vo	VIN	VDD					+25			UN
	(V)	(V)	(V)	-55	-40	+85	+125	Min.	Тур.	Max.	1
Quiescent Device	-	0,5	5	0.25	0.25	7.5	7.5	-	0.01	0.25	
Current,	-	0,10	10	0.5	0.5	15	15	T	0.01	0.5	
IDD Max.	- 51	0,15	15	.1	1	30	30	-	0.01	1	μ
	-	0,20	20	5	5	150	150	-	0.02	5	
Output Low	0,4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	-	m
(Sink) Current	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	-	
IOL Min.	1.5	0,15	15	4.2	4	2.8	2.4	34	6.8	-	
Output High	4.6	0,5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	-	
(Source)	2.5	0,5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2		
Current, IOH Min.	9.5	0,10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	-	
IOH IVIII.	13.5	0,15	15	-4.2	-4	-2.8	-2.4	-3.4	-6.B	-	
Output Voltage:	-	0,5	5	0.05				-	0	0.05	v
Voi Max.	-	0,10	10	0.05				-	0	0.05	
AOT Wax	- 14	0,15	15	0.05				-	0	0.05	
Output Voltage:		0,5	5	4.95			4.95	5	- 1		
High-Level,	-	0,10	10	9.95			9.95	10			
VOH Min.	-	0,15	15	14.95				14.95	15	-	
Voltage, VIL Max.	0.5,4.5	-	5	1.5				-	1.5		
	1,9	-	10	3					3		
	1.5,13.5	-	15	4			-	-	4		
Input High Voltage, VIH Min.	0.5	-	5	3.5			3.5		-		
	1	-	10	7			7	-			
	1.5	-	15	II II				-			
Input Current		0.18	18	+0.1	10.1	-11	21	-	110-5	10.1	ui

CD4001B, CD4002B, CD4025B Types

- Propagation delay time = 60 ns (typ.) at C_L = 50 pF, V_{DD} = 10 V
- Buffered inputs and outputs
- # Standardized symmetrical output characteristic 100% tested for maximum quiescent current at 20 V
- = 5-V, 10-V, and 15-V parametric ratings ■ Maximum input current of 1 µA at 18 V
- over full package-temperature range; 100 nA at 18 V and 25°C
- · Noise margin (over full package temperature

1 V at VDD = 5 V 2 V at VDD = 10 V 2.5 V at VDD = 15 V

Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of "B" Series CMOS Devices"



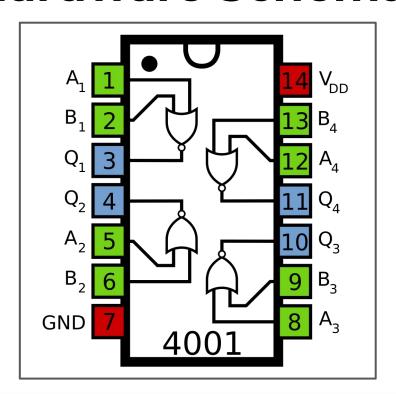




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STATIC ELECTRICAL CHARACTERISTICS

- 05 5

0,10 10

0.10 10

0,15 15

0,18 18

0.15 15

CHARACTER

Quiescent Devic

IDD Max Output Low (Sink) Currer IOL Min.

Output Voltage

VOL Max.

Output Voltage

VON Min.

nput High Voltage

CD4001B, CD4002B, CD4025B Types

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0.01 0.5

2.5 V at VDD = 15 V



LIMITS AT INDICATED TEMPERATURES (°C)

 VO (V)
 V_{IN} (V)
 V_O (V)
 -55
 -40
 +85
 +125
 Min.
 Typ.
 Max.

 0,5
 5
 0.25
 0.25
 7.5
 7.5
 0.01
 0.25

13.5 0.15 15 -4.2 -4 -2.8 -2.4 -3.4 -6.8

4.95

0.05

14.95









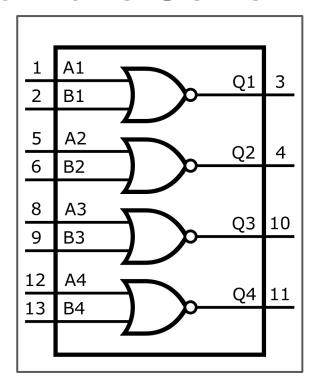


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110-5 10.1 µA

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STATIC FLECTRICAL CHARACTERISTICS

- 05 5

- 0.15 15 - 0.5 5

1,9 - 10

0.5 - 5

0,10 10

0.10 10

0,15 15

0,18 18

CHARACTER

Quiescent Device

IDD Max

Output Low (Sink) Currer IOL Min.

Output Voltage

VOL Max.

Output Voltage

VON Min.

nput High

Voltage

CD4001B, CD4002B, CD4025B Types

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- over full package-temperature range; 100 nA at 18 V and 25°C

LIMITS AT INDICATED TEMPERATURES (°C)

(V) (V) (V) -55 -40 +85 +125 Min. Typ. Max. - 0,5 5 0.25 0.25 7.5 7.5 - 0.01 0.25

13.5 0.15 15 -4.2 -4 -2.8 -2.4 -3.4 -6.8 -

4.95

9.95

14.95

- 0,10 10 0.5 0.5 15 15

· Noise margin (over full package temperature

1 V at VDD = 5 V 2 V at VDD = 10 V

2.5 V at VDD = 15 V

Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of "B" Series CMOS Devices"

0.01 0.5











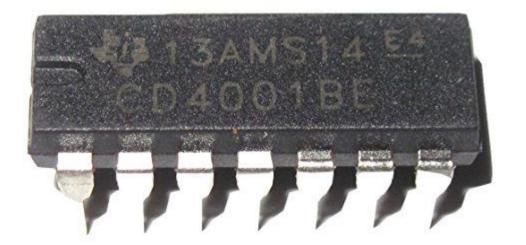
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0 0.05

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110-5 10.1 µA





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IDD Max.	- 51	0,15	15	.1	1	30	30	-	0.01	1	μ
	-	0,20	20	5	5	150	150	-	0.02	5	
Output Low	0,4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	-	m
(Sink) Current	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	-	
IOL Min.	1.5	0,15	15	4.2	4	2.8	2.4	34	6.8	-	
Output High	4.6	0,5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	-	
(Source)	2.5	0,5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2		
Current, IOH Min.	9.5	0,10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	-	
OH win.	13.5	0,15	15	-4.2	-4	-2.8	-2.4	-3.4	-6.8	-	
Output Voltage:	-	0,5	5	0.05				-	0	0.05	v
Low-Level,	-	0,10	10	0.05				-	0	0.05	
VOL Max.	- 12	0,15	15	0.05				-	0	0.05	
Output Voltage:		0,5	5	4.95			4.95	5	-		
High-Level,	-	0,10	10	9.95				9.95	10	-	
VOH Min.	2 -	0,15	15	14.95				14.95	15	-	
Voltage, VIL Max.	0.5,4.5	-	5	1.5					-	1.5	v
	1,9	-	10	3						3	
	1.5,13.5	-	15	4			-	-	4		
Input High Voltage, VIH Min.	0.5	-	5	3.5			3.5		-		
	1	-	10	7			7	-	-0		
	1.5	-	15			11		11			
Input Current		0,18	18	:0.1	10.1	11	11	-	110-5	10.1	ul

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Binary Addition



Binary Addition

Half Adder:



A	В	A + B	SUM	CARRY



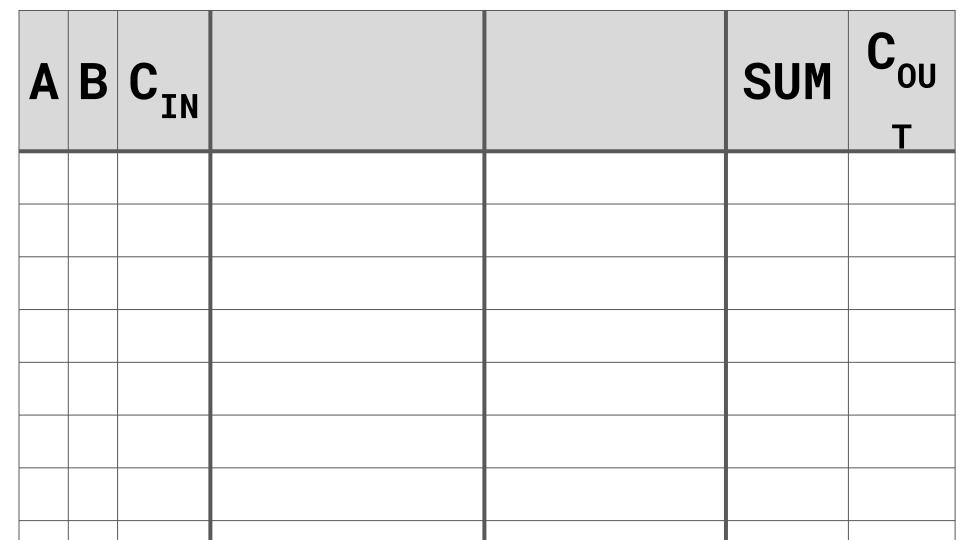
Half Adder Circuit Diagram



Binary Addition

Full Adder:



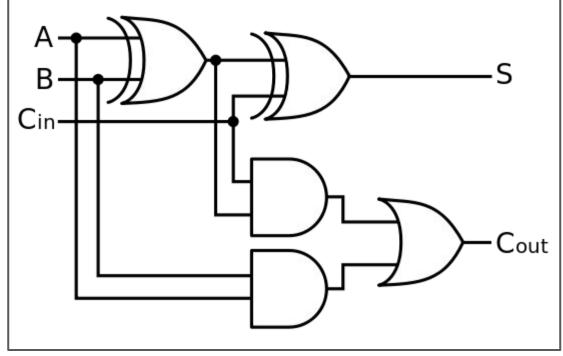


Full Adder Circuit Diagram



Full Adder Circuit Diagram

...or, with only "simple gates":





What more do we need?



Ripple Carry Adder (RCA)



Disadvantages



